

PATENT  
Attorney Docket No. ASC-025DV2C1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANTS: Cheng et al.  
SERIAL NO.: 10/802,186 GROUP NO.: Not yet assigned  
FILING DATE: March 17, 2004 EXAMINER: Not yet assigned  
TITLE: PROCESS FOR PRODUCING SEMICONDUCTOR ARTICLE USING  
GRADED EPITAXIAL GROWTH

**CERTIFICATE OF FIRST CLASS MAILING UNDER 37 C.F.R. 1.8**

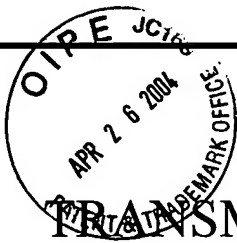
I hereby certify that this correspondence, and any document(s) referred to as enclosed herein, is/are being deposited with the United States Postal Service as first class mail, postage prepaid, in an envelope addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on this 23<sup>rd</sup> day of April, 2004.

  
Wendy Martin

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Submitted herewith are: Transmittal Form (1 page); Information Disclosure Statement (2 pages); Form PTO-1449 (17 pages); and a return receipt postcard.



# TRANSMITTAL FORM

Application Serial Number	10/802,186
Filing Date	March 17, 2004
First Named Inventor	Cheng
Group Art Unit	Not yet assigned
Examiner Name	Not yet assigned
Attorney Docket No.	ASC-025DV2C1
Patent No.	Not applicable
Issue Date	Not applicable

## ENCLOSURES (check all that apply)

<input type="checkbox"/> Fee Transmittal Form <input type="checkbox"/> Check Attached <input type="checkbox"/> Copy of Fee Transmittal Form <input type="checkbox"/> Amendment/Response <input type="checkbox"/> Preliminary <input type="checkbox"/> After Final <input type="checkbox"/> Affidavits/declaration(s) <input type="checkbox"/> Letter to Official Draftsperson including Drawings [Total Sheets _____] <input type="checkbox"/> Petition for Extension of Time <input checked="" type="checkbox"/> Information Disclosure Statement <input checked="" type="checkbox"/> Form PTO-1449 <input type="checkbox"/> Copies of IDS Citations <input type="checkbox"/> Certified Copy of Priority Document(s) <input type="checkbox"/> Sequence Listing submission <input type="checkbox"/> Paper Copy/CD <input type="checkbox"/> Computer Readable Copy <input type="checkbox"/> Statement verifying identity of above	<input type="checkbox"/> Copy of Notice to File Missing Parts of Application <input type="checkbox"/> Formal Drawing(s) <input type="checkbox"/> Request For Continued Examination (RCE) Transmittal <input type="checkbox"/> Power of Attorney (Revocation of Prior Powers) <input type="checkbox"/> Terminal Disclaimer <input type="checkbox"/> Executed Declaration and Power of Attorney for Utility or Design Patent Application <input type="checkbox"/> Small Entity Statement <input type="checkbox"/> CD(s) for large table or computer program <input type="checkbox"/> Amendment After Allowance <input type="checkbox"/> Request for Certificate of Correction <input type="checkbox"/> Certificate of Correction (in duplicate)	<input type="checkbox"/> Notice of Appeal to Board of Patent Appeals and Interferences <input type="checkbox"/> Appeal Brief (in triplicate) <input type="checkbox"/> Status Inquiry <input checked="" type="checkbox"/> Return Receipt Postcard <input checked="" type="checkbox"/> Certificate of First Class Mailing under 37 C.F.R. 1.8 <input type="checkbox"/> Certificate of Facsimile Transmission under 37 C.F.R. 1.8 <input type="checkbox"/> Additional Enclosure(s) (please identify below)
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## CORRESPONDENCE ADDRESS

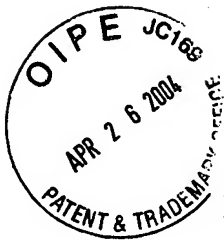
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## SIGNATURE BLOCK

Respectfully submitted,

Date: April 23, 2004  
Reg. No. 44,381  
Tel. No.: (617) 310-8327  
Fax No.: (617) 790-0253

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PATENT  
Attorney Docket No. ASC-025DV2C1

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Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with the provisions of 37 C.F.R. 1.97 and 1.98, Applicants hereby make of record the patents and publications listed on the accompanying Form PTO-1449, and other information contained herein, for consideration by the Examiner in connection with the examination of the above-identified patent application. Each of the references were previously cited in U.S. Patent Application Serial No. 10/379,355 from which this application claims priority. Accordingly, pursuant to 37 C.F.R. § 1.98(d), Applicants have not supplied copies of the references cited on the attached Form PTO-1449, but shall do so upon request.

REMARKS

In accordance with the provisions of 37 C.F.R. 1.97, this statement is being filed (CHECK ONE):

- ☒ (1) within three (3) months of the **filing date** of a national application other than a continued prosecution application under 37 C.F.R. 1.53(d), or within three (3) months of the **date of entry of the national stage** as set forth in 37 C.F.R. 1.491 in an international application, or before the mailing of the **first Office action** on the merits, or before the mailing of a **first Office action** after the filing of a request for continued examination under 37 C.F.R. 1.114; or
- ☐ (2) after the period defined in (1) but before the mailing date of a **final action** or a **notice of allowance** under 37 C.F.R. 1.311, and
- ☐ the requisite Statement is below, **OR**
- ☐ the requisite fee under 37 C.F.R. 1.17(p), namely **\$180.00**, is included herein, or

- ☐ (3) after the mailing date of a **final action** or **notice of allowance** but before the payment of the **issue fee**, **AND**
- ☐ the requisite Statement is below, **AND**
- ☐ the requisite petition fee under 37 C.F.R. 1.17(p), namely **\$180.00** is included herein.

In addition, Applicants wish to bring to the Examiner's attention the following co-pending patent application and office actions issued therein:

U.S. Serial No. 10/802,185, filed on 03/17/2004, by Cheng *et al.*

It is respectfully requested that each of the patents and publications listed on the attached Form PTO-1449, and other information contained herein, be made of record in this application.

Respectfully submitted,



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FORM PTO - 1449

INFORMATION DISCLOSURE STATEMENT

ATTY DOCKET NO.: ASC-025DV2C1

APPLICANTS: Cheng *et al.*

SERIAL NO.: 10/802,186

FILING DATE: March 17, 2004

GROUP: Not yet assigned

## U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A1	4,010,045	03/01/1977	Ruehrwein			
	A2	4,704,302	11/03/1987	Bruel <i>et al.</i>			
	A3	4,710,788	12/01/1987	Dämbkes <i>et al.</i>			
	A4	4,987,462	01/22/1991	Kim <i>et al.</i>			
	A5	4,990,979	02/05/1991	Otto			
	A6	4,997,776	03/05/1991	Haramé <i>et al.</i>			
	A7	5,013,681	05/07/1991	Godbey <i>et al.</i>			
	A8	5,155,571	10/13/1992	Wang <i>et al.</i>			
	A9	5,166,084	11/24/1992	Pfiester			
	A10	5,177,583	01/05/1993	Endo <i>et al.</i>			
	A11	5,202,284	04/13/1993	Kamins <i>et al.</i>			
	A12	5,207,864	05/04/1993	Bhat <i>et al.</i>			
	A13	5,208,182	05/04/1993	Narayan <i>et al.</i>			
	A14	5,212,110	05/18/1993	Pfiester <i>et al.</i>			
	A15	5,221,413	06/22/1993	Brasen <i>et al.</i>			
	A16	5,240,876 A	08/31/1993	Gaul <i>et al.</i>			
	A17	5,241,197	08/31/1993	Murakami <i>et al.</i>			
	A18	5,250,445	10/05/1993	Bean <i>et al.</i>			
	A19	5,285,086	02/08/1994	Fitzgerald			
	A20	5,291,439	03/01/1994	Kauffmann <i>et al.</i>			
	A21	5,298,452	03/29/1994	Meyerson			
	A22	5,310,451	05/10/1994	Tejwani <i>et al.</i>			
	A23	5,316,958	05/31/1994	Meyerson			
	A24	5,346,848	09/13/1994	Gruppen-Shemansky <i>et al.</i>			
	A25	5,374,564	12/20/1994	Bruel			
	A26	5,399,522	03/21/1995	Ohori			
	A27	5,413,679	05/09/1995	Godbey			

EXAMINER

DATE CONSIDERED

<b>FORM PTO – 1449</b>  <b>INFORMATION DISCLOSURE STATEMENT</b>				ATTY DOCKET NO.:    ASC-025DV2C1 APPLICANTS:            Cheng <i>et al.</i> SERIAL NO.:            10/802,186 FILING DATE:          March 17, 2004 GROUP:                  Not yet assigned			
<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
	A28	5,424,243	06/13/1995	Takasaki			
	A29	5,426,069	06/20/1995	Selvakumar et al.			
	A30	5,426,316	06/20/1995	Mohammad			
	A31	5,442,205	08/15/1995	Brasen et al.			
	A32	5,461,243	10/24/1995	Ek et al.			
	A33	5,461,250	10/24/1995	Burghartz et al.			
	A34	5,462,883	10/31/1995	Dennard et al.			
	A35	5,476,813	12/19/1995	Naruse			
	A36	5,479,033	12/26/1995	Baca et al.			
	A37	5,484,664	01/16/1996	Kitahara et al.			
	A38	5,523,243	06/04/1996	Mohammad			
	A39	5,523,592	06/04/1996	Nakagawa et al.			
	A40	5,534,713	07/09/1996	Ismail et al.			
	A41	5,536,361	07/16/1996	Kondo et al.			
	A42	5,540,785	07/30/1996	Dennard et al.			
	A43	5,596,527	01/21/1997	Tomioka et al.			
	A44	5,617,351	04/01/1997	Bertin et al.			
	A45	5,630,905	05/20/1997	Lynch et al.			
	A46	5,659,187	08/19/1997	Legoues et al.			
	A47	5,683,934	11/04/1997	Candelaria			
	A48	5,698,869	12/16/1997	Yoshimi et al.			
	A49	5,714,777	02/03/1998	Ismail et al.			
	A50	5,728,623	03/17/1998	Mori			
	A51	5,739,567	04/14/1998	Wong			
	A52	5,759,898	06/02/1998	Ek et al.			
	A53	5,777,347	07/07/1998	Bartelink			
	A54	5,786,612	07/28/1998	Otani et al.			
<b>EXAMINER</b>				<b>DATE CONSIDERED</b>			

<b>FORM PTO – 1449</b>				<b>ATTY DOCKET NO.:</b> ASC-025DV2C1			
<b>INFORMATION DISCLOSURE STATEMENT</b>				<b>APPLICANTS:</b> Cheng <i>et al.</i>			
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<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A55	5,786,614	07/28/1998	Chuang et al.			
	A56	5,792,679	08/11/1998	Nakato			
	A57	5,808,344	09/15/1998	Ismail et al.			
	A58	5,847,419	12/08/1998	Imai et al.			
	A59	5,863,830	01/26/1999	Bruel et al.			
	A60	5,877,070	03/02/1999	Goesele et al.			
	A61	5,882,987	03/16/1999	Srikrishnan			
	A62	5,891,769	04/06/1999	Hong et al.			
	A63	5,906,708	05/25/1999	Robinson et al.			
	A64	5,906,951	05/25/1999	Chu et al.			
	A65	5,912,479	06/15/1999	Mori et al.			
	A66	5,943,560	08/24/1999	Chang et al.			
	A67	5,963,817	10/05/1999	Chu et al.			
	A68	5,966,622	10/12/1999	Levine et al.			
	A69	5,993,677	11/30/1999	Biasse et al.			
	A70	5,998,807	12/07/1999	Lustig et al.			
	A71	6,013,134	01/11/2000	Chu et al.			
	A72	6,013,563	01/11/2000	Henley et al.			
	A73	6,020,252	02/01/2000	Aspar et al.			
	A74	6,033,974	03/07/2000	Henley et al.			
	A75	6,033,995	03/07/2000	Muller			
	A76	6,058,044	05/02/2000	Sugiura et al.			
	A77	6,059,895	05/09/2000	Chu et al.			
	A78	6,074,919	06/13/2000	Gardner et al.			
	A79	6,096,590	08/01/2000	Chan et al.			
	A80	6,103,559	08/15/2000	Gardner et al.			
	A81	6,103,597	08/15/2000	Aspar et al.			
<b>EXAMINER</b>				<b>DATE CONSIDERED</b>			

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A82	6,103,599	08/15/2000	Henley et al.			
	A83	6,107,653	08/22/2000	Fitzgerald			
	A84	6,111,267	08/29/2000	Fischer et al.			
	A85	6,117,750	09/12/2000	Bensahel et al.			
	A86	6,130,453	10/10/2000	Mei, et al.			
	A87	6,133,799	10/17/2000	Favors Jr., et al.			
	A88	6,140,687	10/31/2000	Shimomura et al.			
	A89	6,143,636	11/07/2000	Forbes et al.			
	A90	6,153,495	11/28/2000	Kub et al.			
	A91	6,154,475	11/28/2000	Soref et al.			
	A92	6,160,303	12/12/2000	Fattarusio			
	A93	6,162,688	12/19/2000	Gardner et al.			
	A94	6,162,705	12/19/2000	Henley et al.			
	A95	6,184,111	02/06/2001	Henley et al.			
	A96	6,190,998 B1	02/20/2001	Bruel et al.			
	A97	6,191,007	02/20/2001	Matsui et al.			
	A98	6,191,432	02/20/2001	Sugiyama et al.			
	A99	6,194,722	02/27/2001	Howe et al.			
	A100	6,204,529	03/20/2001	Lung, et al.			
	A101	6,207,977	03/27/2001	Augusto			
	A102	6,210,988	04/03/2001	Howe et al.			
	A103	6,218,677	04/17/2001	Broekaert			
	A104	6,225,192 B1	05/01/2001	Aspar et al.			
	A105	6,232,138	05/15/2001	Fitzgerald et al.			
	A106	6,235,567	05/22/2001	Huang			
	A107	6,242,324	06/05/2001	Kub et al.			
	A108	6,249,022	06/19/2001	Lin, et al.			
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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A109	6,251,751 B1	06/26/2001	Chu et al.			
	A110	6,251,755	06/26/2001	Furukawa et al.			
	A111	6,261,929	07/17/2001	Gehrke et al.			
	A112	6,266,278	07/24/2001	Harari, et al.			
	A113	6,271,551	08/07/2001	Schmitz et al.			
	A114	6,271,726	08/07/2001	Fransis et al.			
	A115	6,290,804 B1	09/18/2001	Henley et al.			02/20/1998
	A116	6,291,321	09/18/2001	Fitzgerald			03/09/1999
	A117	6,303,468 B1	10/16/2001	Aspar et al.			10/16/2001
	A118	6,313,016	11/06/2001	Kibbel et al.			12/22/1999
	A119	6,316,301	11/13/2001	Kant			03/08/200
	A120	6,323,108	11/27/2001	Kub et al.			07/27/1999
	A121	6,326,667 B1	12/04/2001	Sugiyama et al.			09/08/2000
	A122	6,329,063	12/11/2001	Lo et al.			12/11/1998
	A123	6,335,546	01/01/2002	Tsuda et al.			07/30/1999
	A124	6,339,232	01/15/2002	Takagi			09/20/1999
	A125	6,344,417 B1	02/05/2002	Usenko			08/08/2000
	A126	6,346,459 B1	02/12/2002	Usenko et al.			02/02/2000
	A127	6,350,993	02/26/2002	Chu et al.			03/12/1999
	A128	6,352,909 B1	03/05/2002	Usenko			05/26/2000
	A129	6,355,493 B1	03/12/2002	Usenko			06/30/2000
	A130	6,368,733	04/09/2002	Nishinaga			08/05/1999
	A131	6,368,938 B1	04/09/2002	Usenko			06/07/2000
	A132	6,369,438 B1	04/09/2002	Sugiyama et al.			12/22/2000
	A133	6,372,356	04/16/2002	Thornton et al.			04/28/2000
	A134	6,372,593 B1	04/16/2002	Hattori et al.			07/19/2000
	A135	6,372,609 B1	04/16/2002	Aga et al.			10/08/1999
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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A136	6,387,829 B1	05/14/2002	Usenko et al.			04/06/2000
	A137	6,391,740 B1	05/21/2002	Cheung et al.			04/28/1999
	A138	6,399,970	06/04/2002	Kubo et al.			09/19/1997
	A139	6,403,975	06/11/2002	Brunner et al.			04/08/1997
	A140	6,407,406	06/18/2002	Tezuka			06/29/1999
	A141	6,410,371 B1	06/25/2002	Yu et al.			02/26/2001
	A142	6,425,951	07/30/2002	Chu et al.			08/06/1999
	A143	6,429,061	08/06/2002	Rim			07/26/2000
	A144	6,445,016 B1	09/03/2002	An et al.			02/28/2001
	A145	6,448,152 B1	09/10/2002	Henley et al.			07/16/2001
	A146	6,455,397 B1	09/24/2002	Belford			11/09/2000
	A147	6,458,672 B1	10/01/2002	Henley et al.			11/02/2000
	A148	6,475,072 B1	11/05/2002	Canaperi et al.			09/29/2000
	A149	6,514,836 B2	02/04/2003	Belford			06/04/2001
	A150	6,515,335 B1	02/04/2003	Christiansen et al.			01/04/2002
	A151	6,521,041	02/18/2003	Wu et al.			04/09/1999
	A152	6,524,935 B1	02/25/2003	Canaperi et al.			09/29/2000
	A153	6,534,381 B2	03/18/2003	Cheung et al.			01/04/2000
	A154	6,555,839	04/29/2003	Fitzgerald et al.			05/16/2001
	A155	6,573,126	06/03/2003	Cheng et al.			08/10/2001
	A156	6,583,015	06/24/2003	Fitzgerald et al.			08/06/2001
	A157	6,583,437 B2	06/24/2003	Mizuno et al.			03/19/2001
	A158	6,593,191	07/15/2003	Fitzgerald			05/16/2001
	A159	6,593,625 B2	07/15/2003	Christiansen et al.			04/03/2002
	A160	6,596,610 B1	07/22/2003	Kuwabara et al.			11/27/2000
	A161	6,602,613	08/05/2003	Fitzgerald			01/17/2001
	A162	6,603,156	08/05/2003	Rim			03/31/2001
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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A163	6,607,948 B1	08/19/2003	Sugiyama et al.			08/24/2001
	A164	6,624,047 B1	09/23/2003	Sakaguchi et al.			02/01/2000
	A165	6,624,478 B2	09/23/2003	Anderson et al.			01/30/2002
	A166	6,632,724 B2	10/14/2003	Henley et al.			01/13/2000
	A167	6,635,909 B2	10/21/2003	Clark et al.			03/19/2002
	A168	6,645,831 B1	11/11/2003	Shaheen et al.			05/07/2002
	A169	6,649,492 B2	11/18/2003	Chu et al.			02/11/2002
	A170	6,656,271 B2	12/02/2003	Yonchara et al.			12/03/1999
	A171	6,664,169 B1	12/16/2003	Iwasaki et al.			06/05/2000
	A172	6,677,183 B2	01/13/2004	Sakaguchi et al.			01/31/2002
	A173	6,680,240 B1	01/20/2004	Maszara			06/25/2002
	A174	6,680,260 B2	01/20/2004	Akiyama et al.			09/17/2002
	A175	6,690,043 B1	02/10/2004	Usuda et al.			11/22/2000
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				<b>SERIAL NO.:</b> 10/802,186			
				<b>FILING DATE:</b> March 17, 2004			
				<b>GROUP:</b> Not yet assigned			
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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
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	A234	2004/0053477 A1	03/18/2004	Ghyselen et al.			07/09/2003		
<b>FOREIGN PATENT DOCUMENTS</b>									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
	B1	41 01 167	07/23/1992	DE				No	No
	B2	0 514 018	11/19/1992	EP				No	Yes
	B3	0 587 520	03/16/1994	EP				No	Yes
	B4	0 683 522	11/22/1995	EP				No	Yes
	B5	0 828 296	03/11/1998	EP				No	Yes
	B6	0 829 908	03/18/1998	EP				No	Yes
	B7	0 838 858	04/29/1998	EP				No	No
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<b>FOREIGN PATENT DOCUMENTS</b>									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLAS S	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
	B8	1 020 900	07/19/2000	EP				No	Yes
	B9	1 174 928	01/23/2002	EP				No	Yes
	B10	2 342 777	04/19/2000	GB				Yes	Yes
	B11	4-307974	10/30/1992	JP				No	No
	B12	5-166724	07/03/1993	JP				No	Abstract Only
	B13	6-177046	06/24/1994	JP				No	Abstract Only
	B14	7-106446	04/21/1995	JP				No	No
	B15	7-240372	09/12/1995	JP				No	Abstract Only
	B16	10-270685	10/09/1998	JP				No	Yes
	B17	11-233744	08/27/1999	JP				No	No
	B18	2000-021783	01/21/2000	JP				No	Yes
	B19	2000-31491	01/28/2000	JP				No	No
	B20	2001319935	05/11/2000	JP				Yes	Yes
	B21	2002-076334	03/15/2002	JP				No	Yes
	B22	2002-164520	06/07/2002	JP				No	Yes
	B23	2002-289533	10/04/2002	JP				No	Yes
	B24	WO 98/59365	12/30/1998	PCT				No	Yes
	B25	WO 99/53539	10/21/1999	PCT				No	Yes
	B26	WO 00/48239	08/17/2000	PCT				No	Yes
	B27	WO 01/54202	07/26/2001	PCT				No	Yes
	B28	WO 01/99169A2	12/27/2001	PCT				No	Yes
	B29	WO 02/15244 A2	02/21/2002	PCT				No	Yes
	B30	WO 02/27783 A1	04/04/2002	PCT				No	Yes
	B31	WO 02/071495A1	09/12/2002	PCT				No	Yes
<b>EXAMINER</b>				<b>DATE CONSIDERED</b>					

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EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLAS S	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
	B32	WO 02/082514 A1	10/17/2002	PCT				No	Yes
	B33	WO 00/54338	09/14/2000	WO				No	Yes
	B34	WO 01/022482	03/29/2001	WO				No	Yes
	B35	WO 01/93338	12/06/2001	WO				No	Yes
	B36	WO 02/13262	02/14/2002	WO				No	Yes
	B37	WO 02/47168	06/13/2002	WO				No	Yes
	B38	WO 02/071488	09/12/2002	WO				No	Yes
	B39	WO 02/071491	09/12/2002	WO				No	Yes
	B40	WO 04/006311 A2	01/15/2004	WO			07/09/2003		YES
	B41	WO 04/006326 A1	01/15/2004	WO			07/09/2003		YES
	B42	WO 04/006327 A2	01/15/2004	WO			07/09/2003		YES
	B43	WO 04/019403 A2	03/04/2004	WO			08/26/2003		YES
	B44	WO 04/019404 A2	03/04/2004	WO			08/26/2003		YES
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	C23	Fitzgerald et al., "Dislocation dynamics in relaxed graded composition semiconductors," <u>Materials Science and Engineering B67</u> (1999) pp. 53-61.
	C24	Fitzgerald et al., "Relaxed $\text{Ge}_x\text{Si}_{1-x}$ structures for III-V integration with Si and high mobility two-dimensional electron gases in Si," AT&T Bell Laboratories, Murray Hill, NJ 07974 (1992) <u>American Vacuum Society</u> , pp. 1807-1819.
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	C36	Huang et al., (2001) "Carrier Mobility enhancement in strained Si-on-insulator fabricated by wafer bonding", <u>2001 Symposium on VLSI Technology, Digest of Technical Papers</u> , pages 57-58
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	C38	Huang et al., "The Impact of Scaling Down to Deep Submicron on CMOS RF Circuits", <u>IEEE Journal of Solid-State Circuits</u> , Vol. 33, No. 7, July, 1998, pp. 1023-1036.
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<b>OTHER ART, JOURNAL ARTICLES, ETC.</b>		
<b>EXAM. INIT.</b>	<b>OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)</b>	
	C39	<u>IBM Technical Disclosure Bulletin</u> , Volume 32, No. 8A, January 1990, "Optimal Growth Technique and Structure for Strain Relaxation of Si-Ge Layers on Si Substrates", pp. 330-331.
	C40	Ishikawa et al., "Creation of Si-Ge-based SIMOX structures by low energy oxygen implantation," <u>Proceedings 1997 IEEE International SOI Conference</u> (October 1997) pp. 16-17.
	C41	Ishikawa et al., "SiGe-on-insulator substrate using SiGe alloy grown Si(001)," <u>Applied Physics Letters</u> , Vol. 75, No. 7 (August 16, 1999) pp. 983-985.
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	C43	Ismail, "Si/SiGe High-Speed Field-Effect Transistors," <u>Electron Devices Meeting, Washington, D.C.</u> (December 10, 1995) pp. 20.1.1-20.1.4.
	C44	Kearney et al., "The effect of alloy scattering on the mobility of holes in a $\text{Si}_{1-x}\text{Ge}_x$ quantum well," <u>Semicond. Sci Technol.</u> , Vol. 13 (1998) pp. 174-180.
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	C46	Koester et al., "Extremely High Transconductance $\text{Ge/Si}_{0.4}\text{Ge}_{0.6}$ p-MODFET's Grown by UHV-CVD," <u>IEEE Electron Device Letters</u> , Vol. 21, No. 3 (March 2000) pp. 110-112.
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	C53	Larson, "Integrated Circuit Technology Options for RFIC's - Present Status and Future Directions", <u>IEEE Journal of Solid-State Circuits</u> , Vol. 33, No. 3, March 1998, pp. 387-399.
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<b>FORM PTO – 1449</b>		<b>ATTY DOCKET NO.:</b> ASC-025DV2C1	
<b>INFORMATION DISCLOSURE STATEMENT</b>		<b>APPLICANTS:</b> Cheng <i>et al.</i>	
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		<b>GROUP:</b> Not yet assigned	
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